Sensing Material and Sensing Technology Series

CHEMICAL SENSORS SIMULATION AND MODELING

Volume 3 Solid-State Devices

EDITED BY GHENADII KOROTCENKOV

影印版

化学传感器: 仿真与建模

第3卷 固态设备

上册



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Ghenadii Korotcenkov

Chemical Sensors: Simulation and Modeling Volume 3: Solid-State Devices

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PREFACE

This series, Chemical Sensors: Simulation and Modeling, is the perfect complement to Momentum Press's six-volume reference series, Chemical Sensors: Fundamentals of Sensing Materials and Chemical Sensors: Comprehensive Sensor Technologies, which present detailed information about materials, technologies, fabrication, and applications of various devices for chemical sensing. Chemical sensors are integral to the automation of myriad industrial processes and every-day monitoring of such activities as public safety, engine performance, medical therapeutics, and many more.

Despite the large number of chemical sensors already on the market, selection and design of a suitable sensor for a new application is a difficult task for the design engineer. Careful selection of the sensing material, sensor platform, technology of synthesis or deposition of sensitive materials, appropriate coatings and membranes, and the sampling system is very important, because those decisions can determine the specificity, sensitivity, response time, and stability of the final device. Selective functionalization of the sensor is also critical to achieving the required operating parameters. Therefore, in designing a chemical sensor, developers have to answer the enormous questions related to properties of sensing materials and their functioning in various environments. This five-volume comprehensive reference work analyzes approaches used for computer simulation and modeling in various fields of chemical sensing and discusses various phenomena important for chemical sensing, such as surface diffusion, adsorption, surface reactions, sintering, conductivity, mass transport, interphase interactions, etc. In these volumes it is shown that theoretical modeling and simulation of the processes, being a basic for chemical sensor operation, can provide considerable assistance in choosing both optimal materials and optimal configurations of sensing elements for use in chemical sensors. The theoretical simulation and modeling of sensing material behavior during interactions with gases and liquid surroundings can promote understanding of the nature of effects responsible for high effectiveness of chemical sensors operation as well. Nevertheless, we have to understand that only very a few aspects of chemistry can be computed exactly. However, just as not all spectra are perfectly resolved, often a qualitative or approximate computation can give useful insight into the chemistry of studied phenomena. For example, the modeling of surface-molecule interactions, which can lead to changes in the basic properties of sensing materials, can show how these steps are linked with the macroscopic parameters describing the sensor response. Using quantum mechanics calculations, it is possible to determine parameters of the energetic (electronic) levels of the surface, both inherent ones and those introduced by adsorbed species, adsorption complexes, the precursor state, etc. Statistical thermodynamics and kinetics can allow one to link those calculated surface parameters with surface coverage of adsorbed species corresponding to real experimental conditions (dependent on temperature, pressure, etc.). Finally, phenomenological modeling can tie together theoretically calculated characteristics with real sensor parameters. This modeling may include modeling of hot platforms, modern approaches to the study of sensing effects, modeling of processes responsible for chemical sensing, phenomenological modeling of operating characteristics of chemical sensors, etc.. In addition, it is necessary to recognize that in many cases researchers are in urgent need of theory, since many experimental observations, particularly in such fields as optical and electron spectroscopy, can hardly be interpreted correctly without applying detailed theoretical calculations.

Each modeling and simulation volume in the present series reviews modeling principles and approaches particular to specific groups of materials and devices applied for chemical sensing. Volume 1: Microstructural Characterization and Modeling of Metal Oxides covers microstructural characterization using scanning electron microscopy (SEM), transmission electron spectroscopy (TEM), Raman spectroscopy, in-situ high-temperature SEM, and multiscale atomistic simulation and modeling of metal oxides, including surface state, stability, and metal oxide interactions with gas molecules, water, and metals. Volume 2: Conductometric-Type Sensors covers phenomenological modeling and computational design of conductometric chemical sensors based on nanostructured materials such as metal oxides, carbon nanotubes, and graphenes. This volume includes an overview of the approaches used to quantitatively evaluate characteristics of sensitive structures in which electric charge transport depends on the interaction between the surfaces of the structures and chemical compounds in the surroundings. Volume 3: Solid-State Devices covers phenomenological and molecular modeling of processes which control sensing characteristics and parameters of various solid-state chemical sensors, including surface acoustic wave, metal-insulatorsemiconductor (MIS), microcantilever, thermoelectric-based devices, and sensor arrays intended for "electronic nose" design. Modeling of nanomaterials and nanosystems that show promise for solid-state chemical sensor design is analyzed as well. Volume 4: Optical Sensors covers approaches used for modeling and simulation of various types of optical sensors such as fiber optic, surface plasmon resonance, Fabry-Pérot interferometers, transmittance in the mid-infrared region, luminescence-based devices, etc. Approaches used for design and optimization of optical systems aimed for both remote gas sensing and gas analysis chambers for the nondispersive infrared (NDIR) spectral range are discussed as well. A description of multiscale atomistic simulation of hierarchical nanostructured materials for optical chemical sensing is also included in this volume. *Volume 5: Electrochemical Sensors* covers modeling and simulation of electrochemical processes in both solid and liquid electrolytes, including charge separation and transport (gas diffusion, ion diffusion) in membranes, proton–electron transfers, electrode reactions, etc. Various models used to describe electrochemical sensors such as potentiometric, amperometric, conductometric, impedimetric, and ionsensitive FET sensors are discussed as well.

I believe that this series will be of interest of all who work or plan to work in the field of chemical sensor design. The chapters in this series have been prepared by well-known persons with high qualification in their fields and therefore should be a significant and insightful source of valuable information for engineers and researchers who are either entering these fields for the first time, or who are already conducting research in these areas but wish to extend their knowledge in the field of chemical sensors and computational chemistry. This series will also be interesting for university students, post-docs, and professors in material science, analytical chemistry, computational chemistry, physics of semiconductor devices, chemical engineering, etc. I believe that all of them will find useful information in these volumes.

G. Korotcenkov

ABOUT THE EDITOR

Ghenadii Korotcenkov received his Ph.D. in Physics and Technology of Semiconductor Materials and Devices in 1976, and his Habilitate Degree (Dr. Sci.) in Physics and Mathematics of Semiconductors and Dielectrics in 1990. For a long time he was a leader of the scientific Gas Sensor Group and manager of various national and international scientific and engineering projects carried out in the Laboratory of Micro- and Optoelectronics, Technical University of Moldova. Currently, Dr. Korotcenkov is a research professor at the Gwangju Institute of Science and Technology, Republic of Korea.

Specialists from the former Soviet Union know Dr. Korotcenkov's research results in the field of study of Schottky barriers, MOS structures, native oxides, and

photoreceivers based on Group III–V compounds very well. His current research interests include materials science and surface science, focused on nanostructured metal oxides and solid-state gas sensor design. Dr. Korotcenkov is the author or editor of 11 books and special issues, 11 invited review papers, 17 book chapters, and more than 190 peer-reviewed articles. He holds 18 patents, and he has presented more than 200 reports at national and international conferences.

Dr. Korotcenkov's research activities have been honored by an Award of the Supreme Council of Science and Advanced Technology of the Republic of Moldova (2004), The Prize of the Presidents of the Ukrainian, Belarus, and Moldovan Academies of Sciences (2003), Senior Research Excellence Awards from the Technical University of Moldova (2001, 2003, 2005), a



fellowship from the International Research Exchange Board (1998), and the National Youth Prize of the Republic of Moldova (1980), among others.

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CHAPTER 1

MOLECULAR MODELING

APPLICATION TO HYDROGEN INTERACTION WITH CARBON-SUPPORTED TRANSITION METAL SYSTEMS

Samir H. Mushrif Gilles H. Peslherbe Alejandro D. Rey

1. INTRODUCTION

Carbon can exhibit different types of orbital hybridization, sp, sp^2 , and sp^3 , thus giving rise to a variety of carbonaceous structures. The most precious form of carbon, diamond, consists of carbon with sp^3 -type hybridization, and it is extremely hard due to its strong covalent bonds. A large family of functional carbonaceous materials, particularly those currently being researched for chemical sensor applications, exhibits sp^2 -type bonding. One of the basic building blocks of these materials, including graphitic carbon, carbon fibers, porous carbons, carbon composites, and fullerenes, is the pentagonal/hexagonal carbon ring. A number of such rings connected to each other, in a plane, form a layer, sometimes referred to as a graphene sheet. The delocalized electrons in these rings impart the graphene sheet with good electrical conductivity along the layer. The size of this layer, its agglomeration, interconnectivity, geometry, stacking, and the presence of

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noncarbon elements vary, thus giving rise to different types of carbon materials (with different structural and functional properties) in the family of sp^2 -bonded carbons. Graphitic carbon consists of large-size layers composed of hexagonal carbons stacked together. Fullerenes are another special type of carbon materials made up entirely of carbon, and the hexagonal (and pentagonal) rings form different shapes such as a hollow sphere, ellipsoid, or cylinder. The spherical fullerenes are called buckminsterfullerenes (or buckyballs), and the cylindrical ones are called nanotubes. These carbon materials, nanotubes in particular, have garnered huge attention in recent years due to their exceptional mechanical, thermal, and electrical properties. Less structured carbon materials are the isotropic carbon-based materials. They also consist of sheets of carbon rings; however, the size of the sheet is too small to lead to an anisotropic structure. Their functionality arises from their porous structure and high surface area, which allows the materials to adsorb gases and liquids. The functionality of all the carbonaceous materials is often enhanced by the addition of an external component. Active carbons are often loaded with active metals. There are two different ways of doping the active carbons with metal. One of the methods is to impregnate the carbons using an aqueous solution of metal precursors (Augustine 1996), and the other method is to mix the metal precursor with the carbon precursor even before the preparation of the carbon material (Basova et al. 2005). It has to be noted that the functionality depends on the amount of loaded metal, and there exists an optimum amount above which the performance may decline (Furimsky 2008).

A significantly important class of functional carbon materials in hydrogeninvolving processes consists of nano-size transition metal clusters anchored on a carbon support. One of the key phenomena governing their functionality is the interaction of hydrogen with these materials. If understanding the functionality of a chemical sensor at the molecular level is the ultimate goal, detailed molecular-level information about the interaction of the gas (hydrogen) with the sensor material is an important milestone in achieving this goal. The nature of hydrogen bonding (physisorption or chemisorption) and the possibility of its dissociation and migration on the material are the key factors to understand (Conner and Falconer 1995; Pajonk 2000; Teschner et al. 2008). Hence, the course of interaction of hydrogen with transition metal-doped carbon-supported materials has received significant attention from researchers (Mitchell et al. 2003; Jewell and Davis 2006; Amorim and Keane 2008; Cheng et al. 2008; Teschner et al. 2008; Zhou et al. 2008), particularly since (1) the sp^2 carbon-based materials such as nanotubes, activated carbon, and activated carbon fibers have been recognized as potential hydrogen-adsorbing materials (Dillon et al. 1997; Poirier et al. 2001; Schimmel et al. 2003, 2004; Takagi et al. 2004; Patchkovskii et al. 2005; Cabria et al. 2006; Strobel et al. 2006; Aga et al. 2007; Henwood and Carey 2007; Shevlin and Guo 2007; Cabria et al. 2008) and (2) transition metal doping has been shown to significantly modify the hydrogen adsorption characteristics of such materials